

IN THE SPECIFICATION:

On page 1, prior to line 4, please add the following new headings and paragraph.

--CROSS-REFERENCE TO RELATED APPLICATIONS

This application for U.S. patent is the U.S. National Stage of International Application Number PCT/FI2004/050176 filed November 24, 2004 and published in English on June 23, 2005 as International Publication Number WO 2005/057655 which claims priority from Finnish Application No. 20035238 filed December 15, 2003.

BACKGROUND OF THE INVENTION--.

On page 4, prior to line 26, please add the following new heading:
--BRIEF DESCRIPTION OF THE DRAWINGS--.

On page 5, prior to line 1, please add the following new heading:
--DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS--.

On page 7, please amend the paragraph beginning on line 13 and ending on page 8, line 2 as follows:

--A loop-structured electroconductive element 205 according to an embodiment illustrated in figure 2 is used for example when the desired structure should be as light-weight as possible. The embodiment of figure 2 is feasible also in a case where the semiconductor component 202 left underneath ~~hethe~~ electroconductive element 205 cannot be covered by the electroconductive element 205. For instance a light emitting diode can be shielded by a loop-structured electroconductive element 205 according to the embodiment illustrated in figure 2, because thus the light emitted by the light emitting diode still has free access in the direction of the shielding. A metal sheet cannot be positioned on top of a light emitting diode without altering, preventing or disturbing the proceeding of light in the direction in question. Also from the point of view of the operation of a photovoltage diode, i.e. in order to make

it generate direct current, the visible light, infrared or ultraviolet energy must hit the photovoltage diode. In the shielding of a photovoltage diode, there is according to an embodiment used a loop-structured electroconductive element that does not cover the component to be shielded, and consequently does not prevent radiation from proceeding to the photovoltage diode to be protected. According to an embodiment, on top of the semiconductor component there is arranged a film that can be permeated only by a certain type of radiation with a certain wavelength. The film according to an embodiment has an electroconductive layer that shields the semiconductor component located underneath it against electrostatic pulses, but is permeable for example to visible light, infrared or ultraviolet radiation. Thus the radiation has free access to proceed to the semiconductor component or out thereof. The electroconductive layer can be diffused so thin that light penetrates the generated electroconductive layer for nearly a hundred percent. A permeable, electroconductive layer can be produced for example by vaporizing a thin metal layer on the film surface.--